

FQD19N10TF

FQD19N10TF Information

www.helsener.com	FQD19N10TF Fairchild/ON Semiconductor Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 100V 15.6A DPAK TO-252-3, DPak (2 Leads + Tab), SC-63 For the pricing/inventory/lead time, please contact us	
For Reference Only	Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

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FQD19N10TF Specifications

Manufacturer Part NumberFQD19N10TFManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C15.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs25nC @ 10VInput Capacitance (Ciss) (Max) @ Vds780pF @ 25VVgs (Max)±25VFET Feature-Power Dissipation (Max)2.5W (Ta), 50W (Tc)Rds On (Max) @ Id, Vgs100 mOhm @ 7.8A, 10V		
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Operating Temperature $-55^{\circ}C \sim 150^{\circ}C (TJ)$		
Mounting Type Surface Mount		
Supplier Device Package D-Pak		
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
	Report errors?	

FQD19N10TF Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

FQD19N10TF Payment Methods



FQD19N10TF Shipping Methods



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